RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

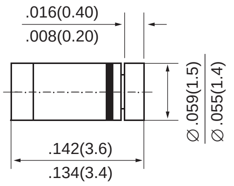
BAS85

SCHOTTKY DIODES

FEATURES

- Fast Switching Device(T_{RR}<4.0nS)
- Mini MELF Glass Case (SOD-80)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All external surfaces are corrosion resistant and leads are readily solderable

SOD-80



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

MAXIMUM RATINGES (@ T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	BAS85	UNITS
Maximum Forward Comtinuous Reverse Voltage	V_R	30	V
Maximum Forward Comtinuous Current @ T_A=25°C	I_F	200	mAmps
Maximum Peak Forward Current @ T_A=25°C	I_{FM}	300	mAmps
Surge Forward Current @ tp<1s,T_A=25°C	I_{FSM}	600	mAmps
Maximum Power Dissipation @ T_A=65°C	P_D	200	mW
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-65 to + 150	°C

ELECTRICAL CHARACTERISTICS (@ T_A = 25°C unless otherwise noted)

CHARACTERISTICS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Reverse breakdown voltage (I_R=10µA)		$V_{(BR)R}$	30	-	-	V
Reverse voltage leakage current (V_R=25V)		I_R	-	-	2	µA
Forward voltage Pulse Tesx tp<300µs,δ<2%	(I_F=0.1mA)	V_F	-	-	0.24	V
	(I_F=1mA)			-	0.32	
	(I_F=10mA)			-	0.4	
	(I_F=30mA)			0.5	-	
	(I_F=100mA)			-	0.8	
Diode capacitance (V_R=1,f=1MHz)		C_D	-	-	10	pF
Reveres recovery time (I_F=I_R=10mA,I_R=1mA)		t_{rr}	-	-	5	nS

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